

IN THE SPECIFICATION

Please amend Paragraphs [0010], [0046] and add new Paragraph [0011.1] as follows:

[0010] Accordingly, an object of the present invention is to provide a method of fabricating a solar cell having an n-type buffer layer providing a heterojunction with a light absorbing layer formed on a back electrode, wherein the buffer layer is formed by CBD (Chemical Bath Deposition) process using a aqueous solution for dipping the light absorbing layer in such a way that particles can be deposited on the light absorbing layer to form a buffer layer of InS, which has a grain structure improved to pass even light of short wavelengths. The CBD process according to the present invention specifically increases sizes of particles to be deposited by ~~increasing temperature of the aqueous solution.~~ conducting a first step of maintaining the solution at a first temperature for a first preset time, a second step of increasing the temperature of the solution from the first temperature to a second higher temperature for a second preset time and a third step of maintaining the solution at the second temperature for a third preset time.

Insert the following new Paragraph after Paragraph [0011] and before Title "BRIEF DESCRIPTION OF THE DRAWINGS".

[0011.1] In this case, according to the present invention, a buffer layer is formed of stepwise deposits of particles of n-type semiconductor material in such manner as the layer has a profile which represents deposits having different pH-values: upper deposits have larger pH value.

[0046] According to the present invention, it is also possible to provide a method of fabricating a thin-film compound solar cell having an n-type buffer layer formed therein for providing a hetero-junction with a p-type compound semiconductor light absorbing layer formed on a back electrode, wherein the buffer layer is formed by applying a chemical bath deposition (CBD) process using an aqueous solution for dipping the light absorbing layer to deposit particles on the surface thereof. The process provides a buffer layer of n-type semiconductor material, which is featured by gradually or step-by-step increased sizes of deposited particles in the outward direction from the light absorbing layer or featured by a structure having upper side deposits of larger pH-values and lower side deposits of smaller pH values. The buffer layer thus formed possesses a high optical transmittance, tight adherence to the light absorbing layer and conformity with the transparent electrode formed thereon though it is made of InS material generally possessing a small band gap and hard to pass light of short wavelengths.